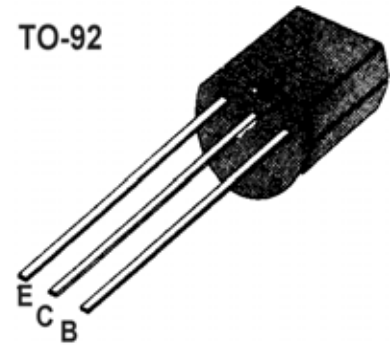


■ ■ APPLICATION: General Purpose Applications.

■ ■ MAXIMUM RATINGS ($T_a=25^\circ\text{C}$)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V_{CBO}	-50	V
Collector-emitter voltage	V_{CEO}	-40	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current	I_C	-150	A
Collector Power Dissipation	P_C	300	W
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55~150	$^\circ\text{C}$


■ ■ ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	h_{FE}	120		820		$V_{CE} = -6V, I_C = -1mA$
Collector Cut-off Current	I_{CBO}			-0.5	μA	$V_{CB} = -30V, I_E = 0$
Emitter Cut-off Current	I_{EBO}			-0.5	μA	$V_{EB} = -3V, I_C = 0$
Collector-Base Breakdown Voltage	BV_{CBO}	-50			V	$I_C = -0.02mA, I_E = 0$
Collector-Emitter Breakdown Voltage	BV_{CEO}	-40			V	$I_C = -1mA, I_B = 0$
Emitter-Base Breakdown Voltage	BV_{EBO}	-5			V	$I_E = -0.02mA, I_C = 0$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			-0.4	V	$I_C = -50mA, I_B = -5mA$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			-1.1	V	$I_C = -50mA, I_B = -5mA$
Gain bandwidth product	f_T		180		MHz	$I_C = -2mA, V_{CE} = -12V$
Common Base Output Capacitance	C_{ob}		4		PF	$V_{CB} = -10V, I_E = 0, f = 1MHz$

■ ■ h_{FE} Classification And Marking

Classification	Q	R	S	E
h_{FE}	120~270	180~390	270~560	390~820